

Electronic Supplementary Information

Vacuum-Deposited Organic Photodetector Utilizing Non-Fullerene Acceptor for Enhanced Detectivity in Green Visible Light Spectrum

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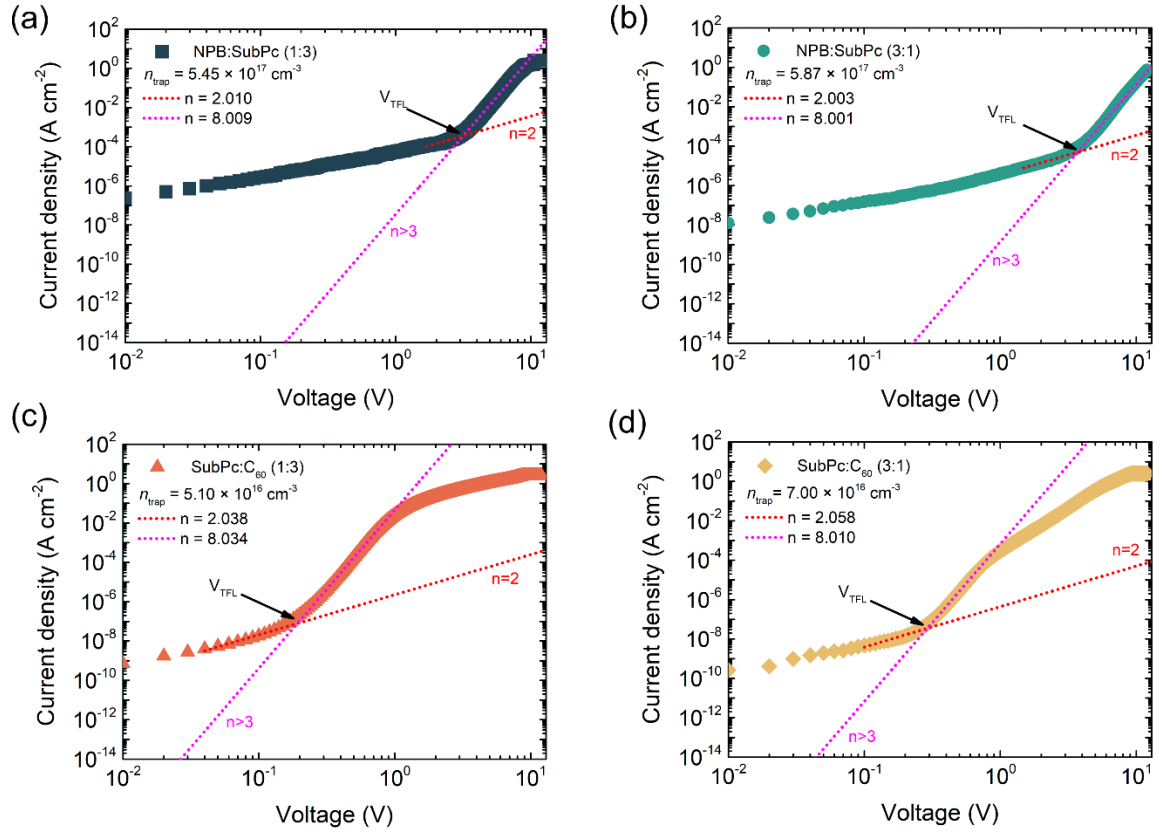


Figure S1 J-V characteristics of the different active layers of OPD devices indicate different regions to obtain trap state density from electron only device.

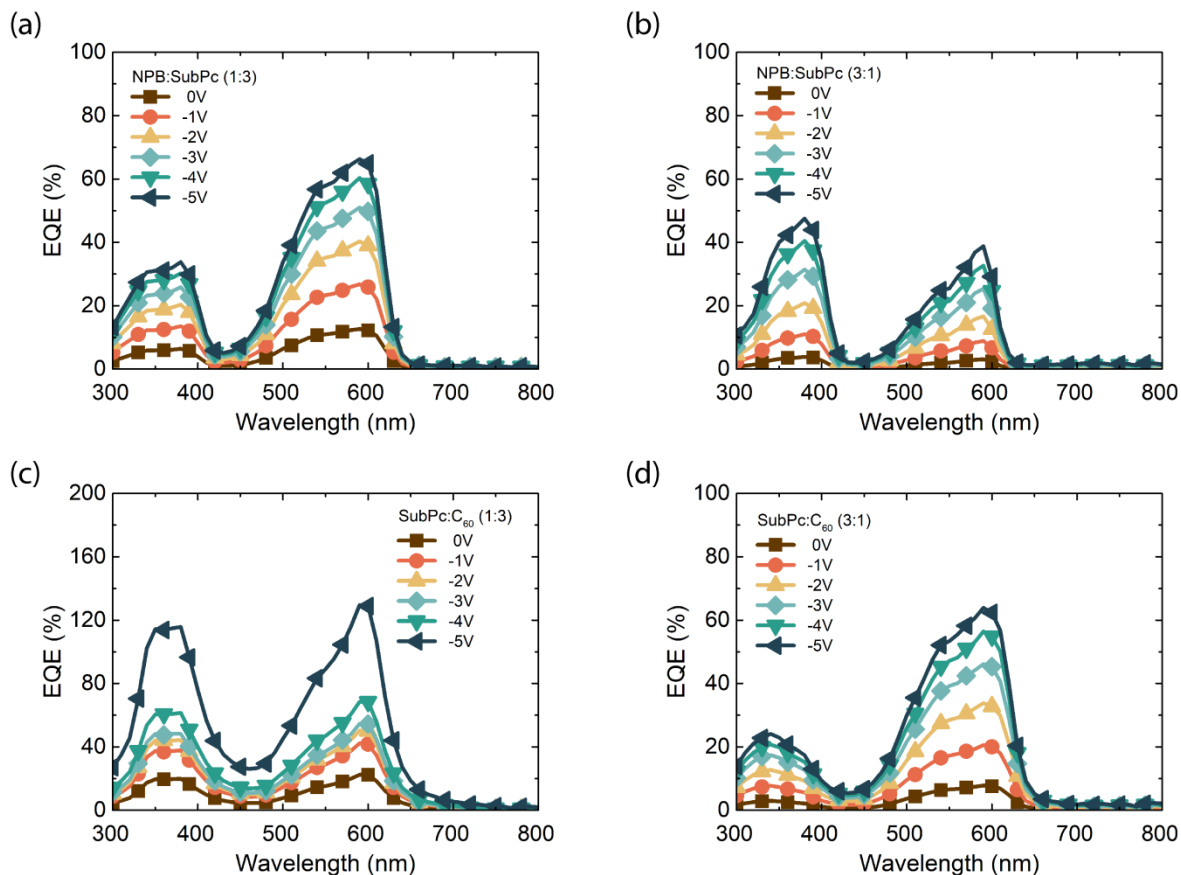


Figure S2 The external quantum efficiency of different active layers of the OPD devices that consist of (a) NPB:SubPc (1:3), (b) NPB:SubPc (3:1), (c) SubPc:C₆₀ (1:3), and (d) SubPc:C₆₀ (3:1).

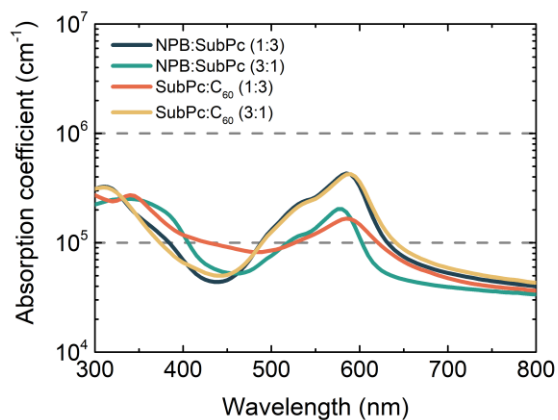


Figure S3 The absorption coefficient spectra from blending of donor and acceptor with different active layers.

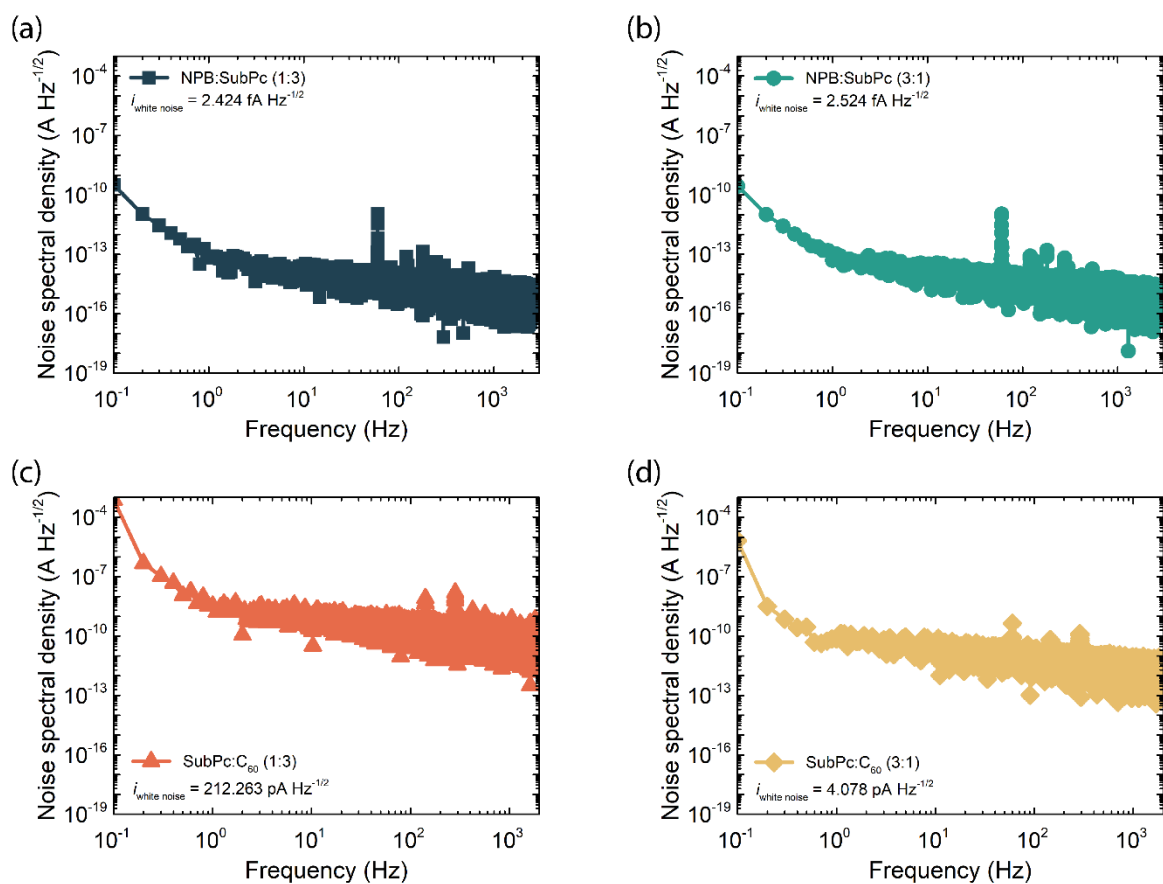


Figure S4 Noise spectral density of different active layers of the OPD devices using bias voltage of -5 V that consist of (a) NPB:SubPc (1:3), (b) NPB:SubPc (3:1), (c) SubPc:C₆₀ (1:3), and (d) SubPc:C₆₀ (3:1).

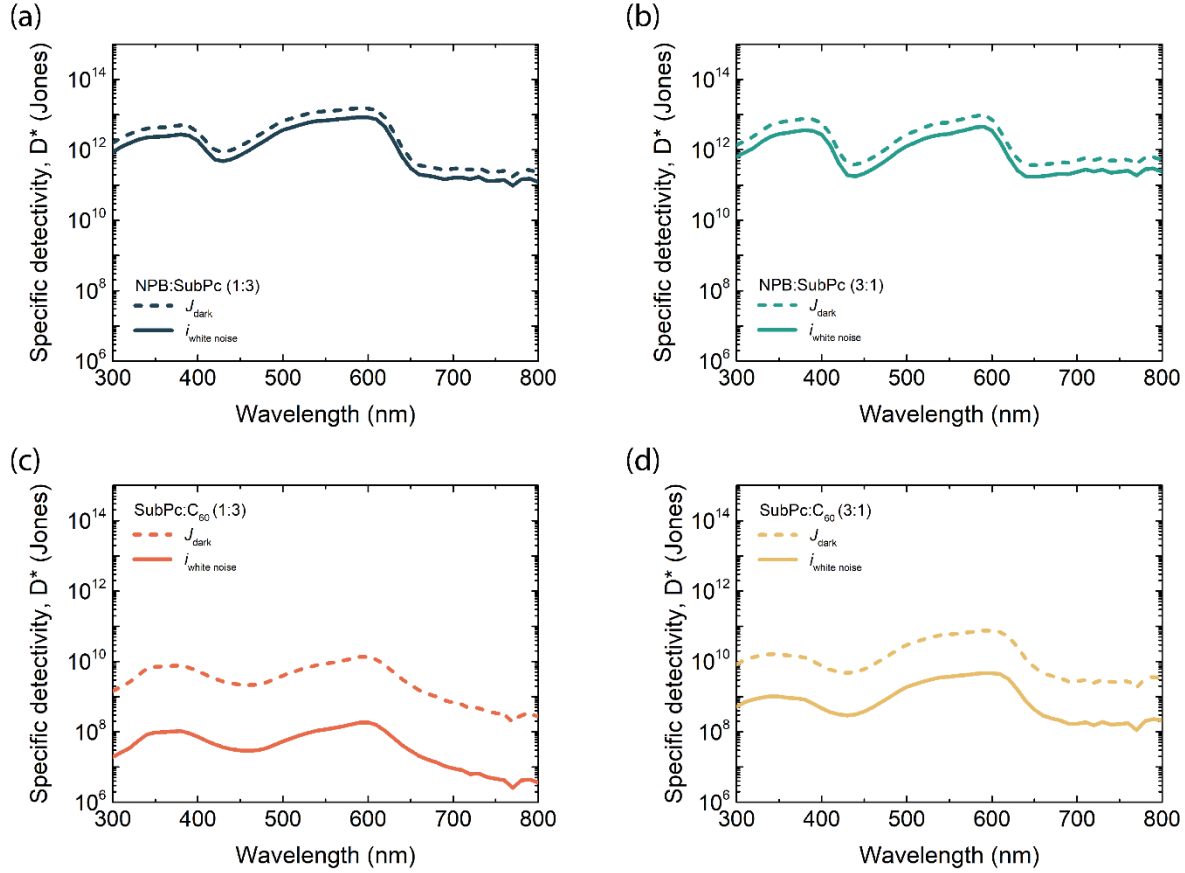


Figure S5 Specific detectivity based on the dark current density and white noise of different active layers of the OPD devices under a bias voltage of -5 V that consist of (a) NPB:SubPc (1:3), (b) NPB:SubPc (3:1), (c) SubPc:C₆₀ (1:3), and (d) SubPc:C₆₀ (3:1).

Table S1 The summary of noise parameters of OPD devices with various active layers.

Device	Active Layer	$I_{\text{shot noise}}$ [A Hz ^{-1/2}] ^a	$I_{\text{white noise}}$ [A Hz ^{-1/2}] ^b	$D^*_{\text{white noise}}$ [Jones] ^c	Min. Irradiance [W cm ⁻²] ^d
A	NPB:SubPc (1:3)	4.12×10^{-15}	2.42×10^{-15}	5.78×10^{12}	4.47×10^{-9}
B	NPB:SubPc (3:1)	3.75×10^{-15}	2.52×10^{-15}	2.43×10^{12}	7.47×10^{-9}
C	SubPc:C ₆₀ (1:3)	9.12×10^{-12}	2.12×10^{-10}	9.38×10^7	1.55×10^{-4}
D	SubPc:C ₆₀ (3:1)	8.07×10^{-13}	4.07×10^{-12}	3.14×10^9	7.29×10^{-6}

^a $I_{\text{shot noise}}$ is calculated by Equation (5), ^b The $i_{\text{white noise}}$ is calculated by using Equation (6), ^c Detectivity is calculated using Equation (7), where $A = 0.04$ cm², $\Delta\delta = 0.1$, along to a wavelength of 530 nm. ^d The minimum irradiance is obtained from Equation (9), which is multiplied and divided by f_{3dB} and A , respectively.